MGBR40L150C

## **Preliminary**

**DIODE** 

# MOS GATED BARRIER RECTIFIER

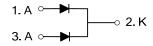
### **■** DESCRIPTION

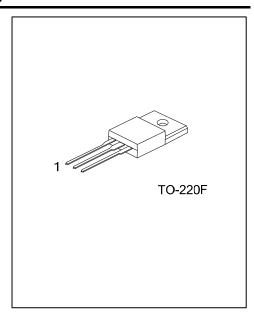
The UTC **MGBR40L150C** is a surface mount mos gatedbarrier rectifier,it uses UTC's advanced technology to provide customers withlow forward voltage drop and high switching speed, etc.

### ■ FEATURES

- \* Low forward voltage drop
- \* High switching speed

## ■ SYMBOL

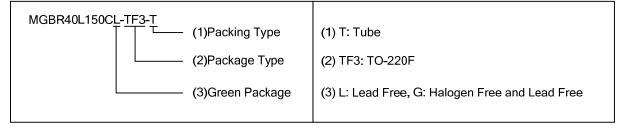




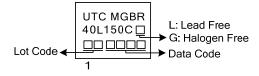
## **■ ORDERING INFORMATION**

Ordering Number		Dealtons	Pin Assignment			Dealing	
Lead Free	Halogen Free	Package	1	2	3	Packing	
MGBR40L150CL-TF3-T	MGBR40L150CG-TF3-T	TO-220F	Α	K	Α	Tube	

Note: Pin Assignment: A: Anode K: Common Cathode



## MARKING



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## ■ **ABSOLUTE MAXIMUM RATINGS** (T<sub>A</sub>=25°C, unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

PARAMETER		SYMBOL	RATINGS	UNIT
Repetitive Peak Reverse Voltage		$V_{RRM}$	150	V
Average Rectified Output Current Per	Per Leg	1	20	Α
Device	Total	IO	40	Α
Non-Repetitive Peak Forward Surge Current 8.3ms		I <sub>FSM</sub>	250	Α
Single Half Sine-Wave Superimposed on	ve Superimposed on Rated Load		200	, ,
Operating Junction Temperature		$T_J$	-65~+150	°C
Storage Temperature		T <sub>STG</sub>	-65~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

### **■ THERMAL CHARACTERISTICS**

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient	$\theta_{JA}$	62.5	°C/W	
Junction to Case	θ <sub>JC</sub>	3.31	°C/W	

## ■ **ELECTRICAL CHARACTERISTICS**(T<sub>A</sub>=25°C,unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	$V_{(BR)R}$	I <sub>R</sub> =0.5mA	150			V
Farmand Valtage Dran	V <sub>FM</sub>	I <sub>F</sub> =20A, T <sub>J</sub> =25°C			0.90	V
Forward Voltage Drop		I <sub>F</sub> =20A, T <sub>J</sub> =125°C			0.82	V
Leakage Current (Note 1)	DM	V <sub>R</sub> =150V, T <sub>J</sub> =25°C			100	μA
		V <sub>R</sub> =150V, T <sub>J</sub> =125°C			15	mA

Notes: 1. Short duration pulse test used to minimize self-heating effect.

<sup>2.</sup> Thermal resistance junction to case mounted on heatsink.

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